

/ Revised record

±100 nA

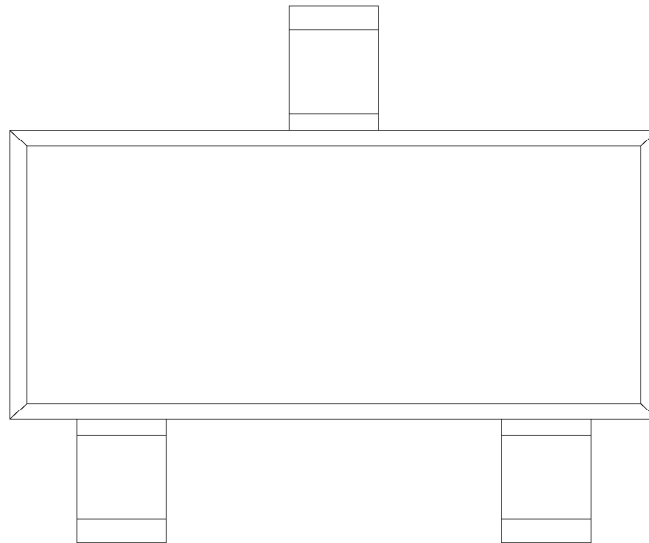
SOT-23 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a SOT-23 Plastic Package.

输出电阻小、性能高；SOT-23 封装，利于设计安装，符合 AEC-Q101 标准高可靠性要求，无卤产品。
Low $R_{DS(on)}$, rugged and reliable, compact industry standard SOT-23 surface mount pac) ac) p

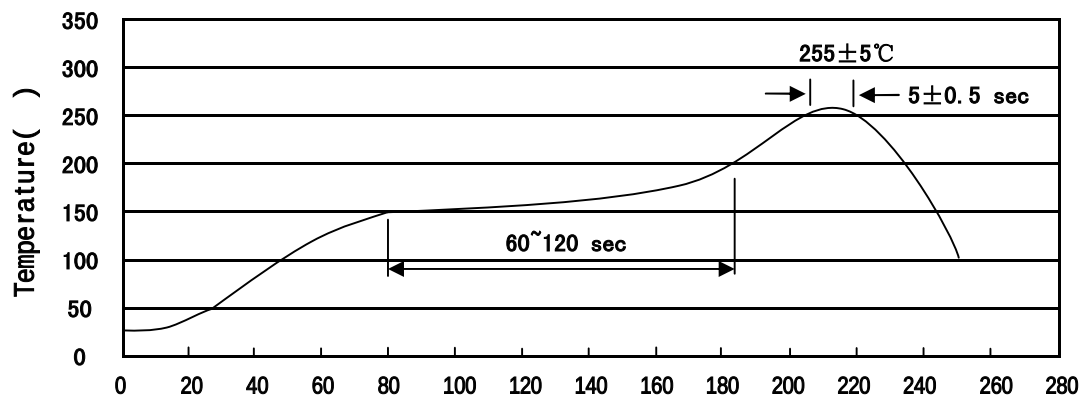
参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	50	V
Gate-Source Voltage	V_{GSS}	± 20	V
Drain Current	I_D	220	mA
Peak Drain Current	I_{DM}	880	mA
Power Dissipation	P_D	360	mW

Thermal Resistance, Junction-to-

/ Marking Instructions



() / Temperature Profile for IR Reflow Soldering(Pb-Free)



说明：

- 1、预热温度 150 ~ 200°C，时间 60 ~ 120sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:150~200°C, Time:60~120sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

/ Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

/ Packaging SPEC.

卷盘包装 / REEL

Package Type	Units					Dimension (unit mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box	Outer Box
SOT-23	3,000	10	30,000	6	180,000	7" x8	180×120×180	390×385×205

/ Notices